

# BRCS18N20FA

Rev.B Aug.-2025

## / Descriptions

TO-220F          N          MOS  
N-CHANNEL MOSFET in a TO-220F Plastic Package.

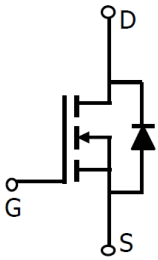
## / Features

$V_{DS}=200V$     $I_D=18A$     $V_{GS}=\pm 20V$   
 $R_{DS(on)}@10V$  170m (Type.130m )  
 $R_{DS(on)}@4.5V$  200m (Type.150m )  
HF Product.

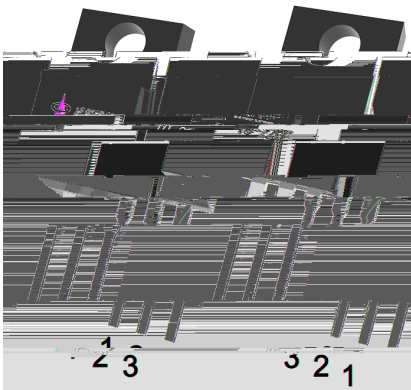
## / Applications

LED  
Networking, Load Switch, LED applications.

## / Equivalent Circuit



## / Pinning



PIN1 G          PIN 2 D          PIN 3 S

## / Marking

See Marking Instructions.

## / Absolute Maximum Ratings(Ta=25 )

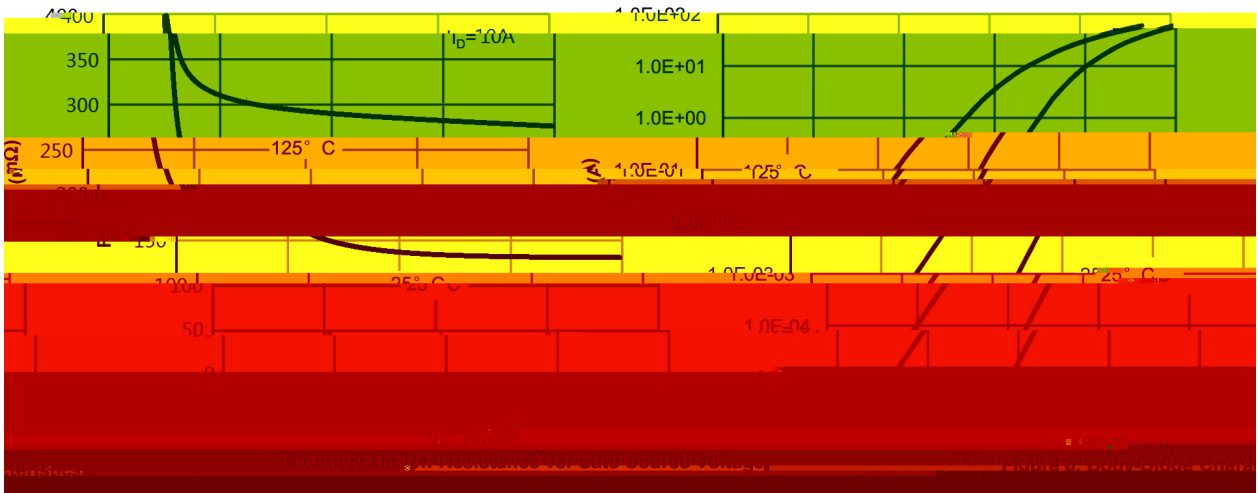
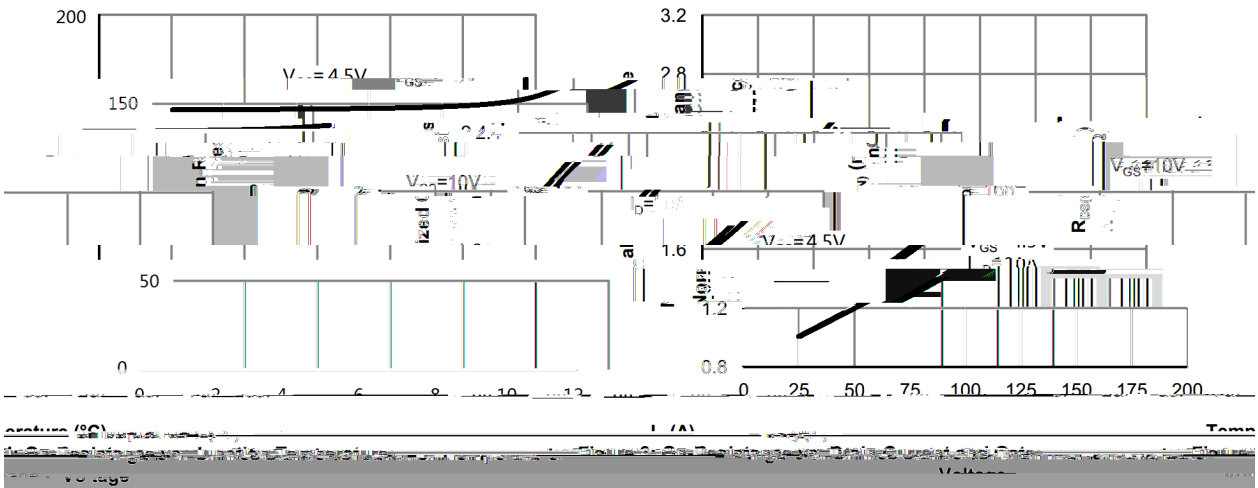
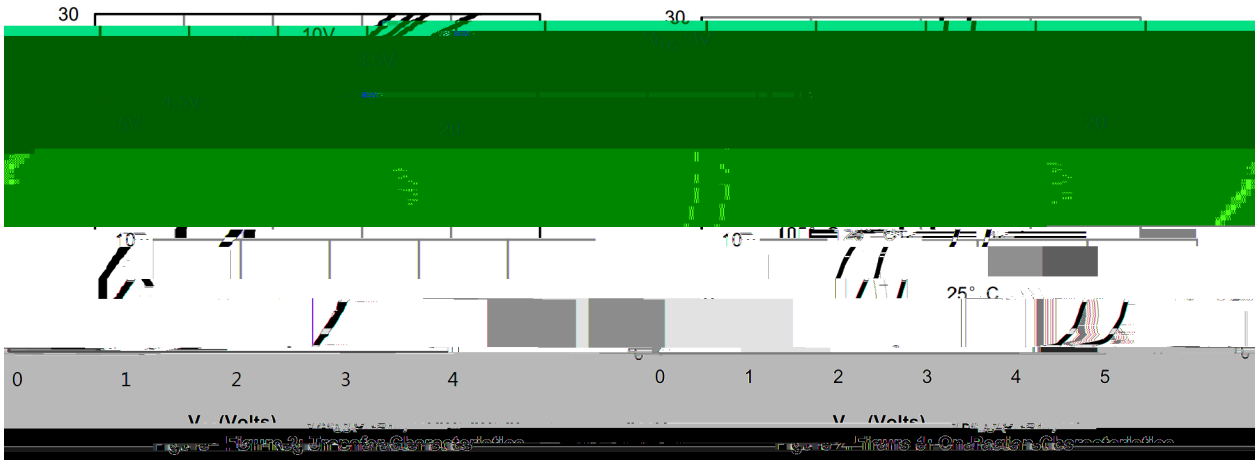
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		$V_{DSS}$	200	V
Drain Current		$I_D(T_C=25)$	18	A
Drain Current - Pulsed		$I_{DM}$	28	A
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Single Pulsed Avalanche Energy(L=10mH)		$E_{AS}$	125	mJ
Avalanche Current(L=10mH)		$I_{AS}$	9.5	A
Power Dissipation		$P_D(T_C=25)$	50	W
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to 150	
Maximum Junction-to-Ambient	t 10s	$R_{JA}$	30	/W
Maximum Junction-to-Ambient	Steady-State		62.5	
Maximum Junction-to-Case	Steady-State	$R_{JC}$	2.5	

## / Electrical Characteristics(Ta=25 )

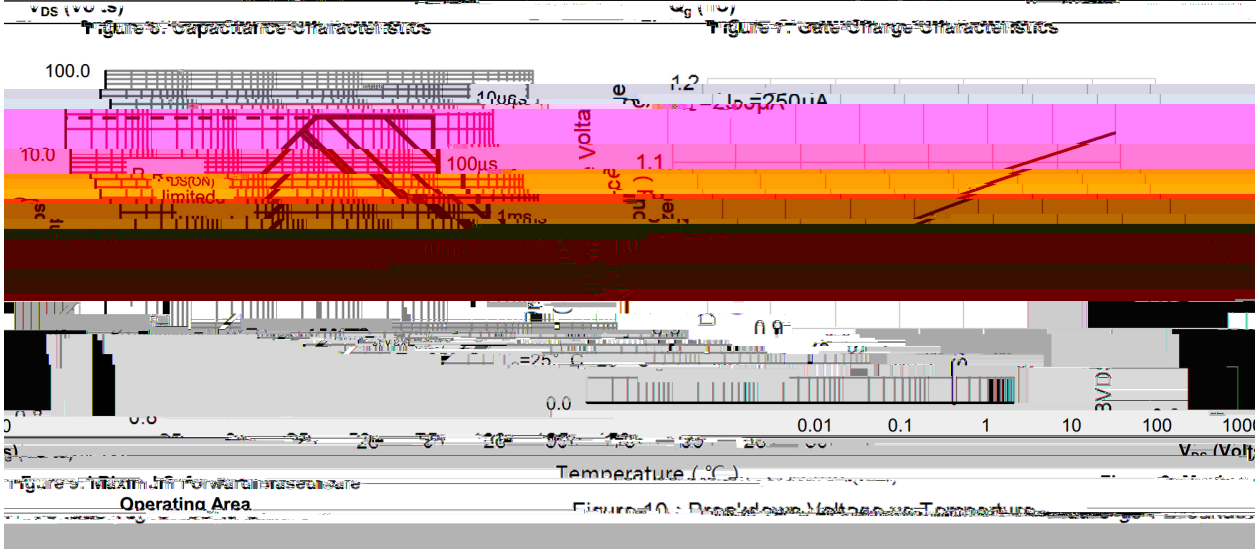
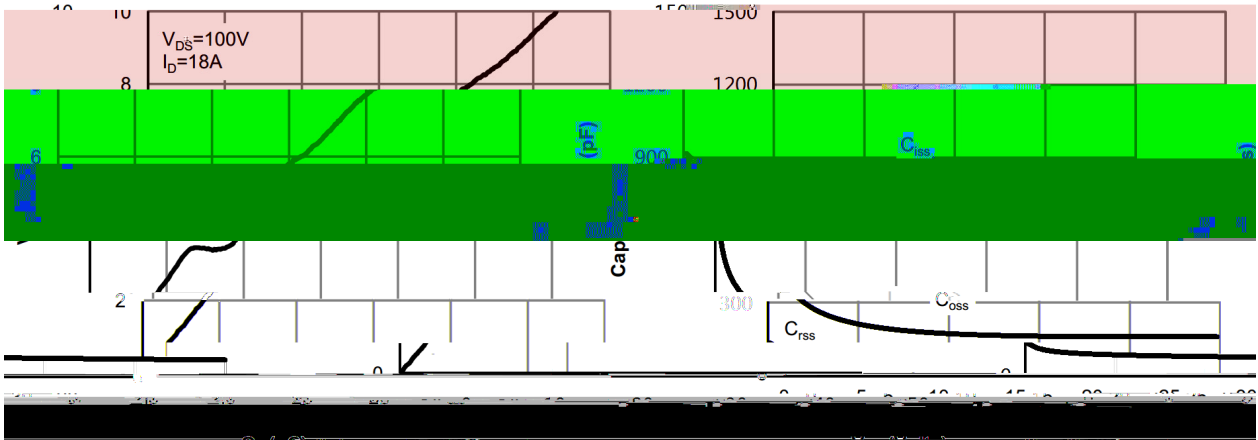
Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V$	$I_D=250\mu A$	200			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=200V$	$V_{GS}=0V$			1	$\mu A$
Gate-Body Leakage Current Forward	$I_{GSS}$	$V_{GS}=\pm 20V$	$V_{DS}=0V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$	$I_D=250\mu A$	1.0	1.5	2.0	V
Total gate charge	$R_{DS(on)}$	$V_{GS}=10V$	$I_D=10A$		130	170	m
		$V_{GS}=4.5V$	$I_D=10A$		150	200	m
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V$	$I_S=1A$			1.2	V
Gate resistance	$R_g$	$V_{GS}=0V$ $f=1MHz$	$V_{DS}=0V,$		6.5		
Input Capacitance	$C_{iss}$	$V_{DS}=25V$ $f=1MHz$	$V_{GS}=0V$		830		pF
Output Capacitance	$C_{oss}$				150		
Reverse Transfer Capacitance	$C_{rss}$				65		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V,$ $I_D=18A$	$V_{DS}=100V,$		27		nC
Total Gate Charge	$Q_{g(4.5V)}$				12		
Gate Source Charge	$Q_{gs}$				7		
Gate Drain Charge	$Q_{gd}$				3		

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=75V$ $R_L=2.5$ $R_{GEN}=3$		8		ns
Turn-On Rise Time	$t_r$			10		
Turn-Off Delay Time	$t$					

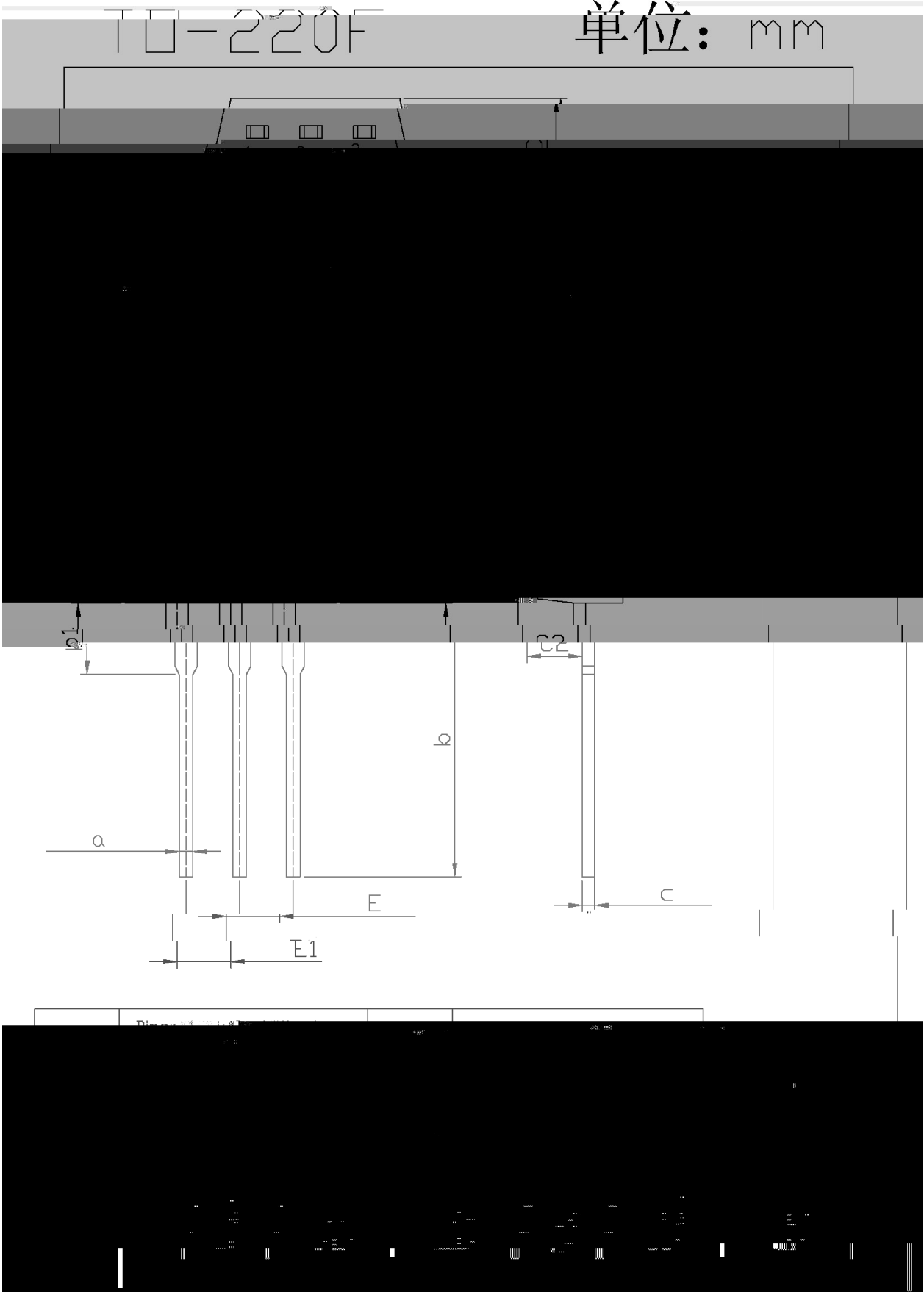
**/ Electrical Characteristic Curve**



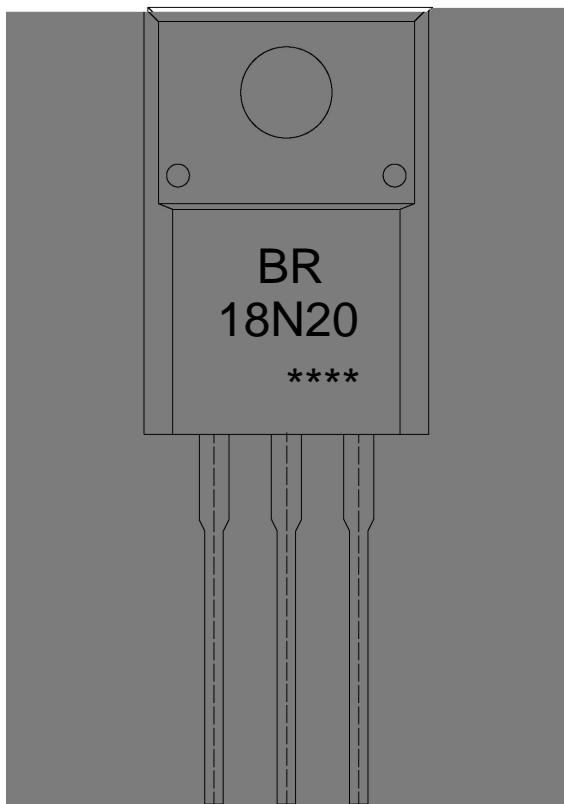
/ Electrical Characteristic Curve



**/ Package Dimensions**



**/ Marking Instructions**



BR

18N20

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Note:

BR: Company Code

18N20: Product Type Code

\*\*\*\*: Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)

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